Amendments to the Specification

Please re-write par. [0035] to read as follows:

[0035] A present attempt to minimize such problems involves processing the inner surface of a cover 20 that faces the hot plate 11 in an oxide so as to roughen its surface. Roughening the surface of the cover 20 is aimed at scattering the heat from the hot plate 11 to thereby maintain the wafer at a uniform temperature. However, the temperature of the hot plate 11 nonetheless remains non-uniform and is lowest at a central portion thereof. Consequently, the CD of the photoresist pattern at the central region C of the wafer W (FIG. 2) is too low in comparison with the CD of the photoresist pattern at the other regions (T, L, R, F) of the wafer. Thus, the photoresist pattern will produce a defect when used to form a fine pattern in a subsequent process such as an etch process.

Please re-write par. [0110] to read as follows:

[0010] The present invention is characterized by enhancing the cover 20, particularly, the inner circumferential surface of the cover 20. To this end, the inner surface of the cover 20 that faces the hot plate 11 is provided with a thin film 30 that is made of material having a low emissivity (ϵ) in the vertical direction, i.e., in a direction perpendicular to the upper surface of the hot plate 11. Preferably, the emissivity (ϵ) of the thin film 30 is within a range of 0.02 ~ 0.05[~~, and more preferably within a range of 0.02 ~ 0.05~~]. To this end, the

surface of the thin film 30 is polished so as to be smooth. For example, the thin film 30 is made of aluminum in the form of a foil. The foil is adhered to the inner surface of the cover 20.

Please re-write par. [0120] to read as follows:

[0120] Referring to FIG. 4, the emissivity of the aluminum which is oxidized, or whose surface is not polished and blunt, is higher than that of the aluminum that is well-polished (smooth). Therefore, well-polished aluminum should be used for the film 30. However, as FIG. 4 shows, brass, copper or gold can be used, wherein such materials [~~are~~] can also be well-polished.

Please re-write par. [0135] to read as follows:

[0135] As can be readily seen from such CD data, the CD varied the least throughout the wafer in the case of the aluminum tape, namely in the case where the material having a low emissivity was disposed over the inner surface of the cover 20 from which heat normally would radiate toward the wafer. Simple structural changes involving the surface did not influence the variations in the CD much. Also, tests in which the color of the inner surface of the cover 20 was changed showed that the color of the surface [~~color~~] never influences the CD of the pattern at various regions of the wafer.

Please re-write par. [0140] to read as follows:

[0140] As was described above regarding the results of various tests conducted in connection with the invention, the greatest influences on the CD of a pattern on a wafer are the material at the inner surface of the cover 20 that faces the hot plate 11, and the roughness of the material. Thus, the thin film 30 is made of material having a low emissivity, e.g., aluminum, copper, brass, gold or even silver, and the surface of the thin film 30 is polished so as to be remarkably smooth.